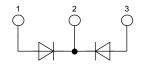
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## **Sonic Fast Recovery Diode**

High Performance Fast Recove Low Loss and Soft Recovery Common Cathode

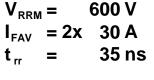
Part number

DHG 60 C 600 HB



### Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)





Backside: cathode

## Package:

- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

### Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RRM</sub>	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}C$			600	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V	$T_{VJ} = 25^{\circ}C$			50	μA
		$V_{R} = 600 V$	$T_{VJ} = 125^{\circ}C$			5	mΑ
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A	$T_{VJ} = 25^{\circ}C$			2.36	V
		$I_F = 60 A$				3.15	٧
		I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 150°C			2.20	V
		$I_F = 60 A$				3.08	V
I <sub>FAV</sub>	average forward current	rectangular, d = 0.5	$T_{c} = 85^{\circ}C$			30	Α
$V_{F0}$	threshold voltage $T_{VJ} = 150$ °C				1.31	٧	
r <sub>F</sub>	slope resistance } for power loss	calculation only				28.6	mΩ
R <sub>thJC</sub>	thermal resistance junction to case					0.70	K/W
T <sub>VJ</sub>	virtual junction temperature			-55		150	°C
$P_{tot}$	total power dissipation		$T_c = 25^{\circ}C$			180	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			200	Α
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25^{\circ}C$		12		Α
		$I_F = 30 \text{ A}; V_R = 400 \text{ V}$	$T_{VJ} = ^{\circ}C$		tbd		Α
t <sub>rr</sub>	reverse recovery time	$-di_F/dt = 600 A/\mu s$	$T_{VJ} = 25^{\circ}C$		35		ns
			$T_{VJ} = ^{\circ}C$		tbd		ns
C¹	junction capacitance	$V_R = 300 V; f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		tbd		pF

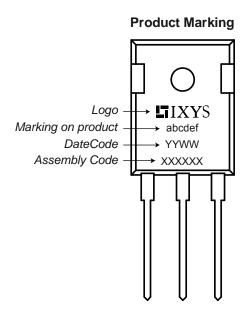


# DHG 60 C 600 HB

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			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per pin 1)			70	Α
R <sub>thCH</sub>	thermal resistance case to heatsink			0.25		K/W
T <sub>stg</sub>	storage temperature		-55	i	150	°C
Weight				6		g
M <sub>D</sub>	mounting torque		0.8	1	1.2	Nm
F <sub>c</sub>	mounting force with clip		20	)	120	N

<sup>1)</sup> I<sub>RMS</sub> is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip. In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



## Part number

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast 60 = Current Rating [A]

C = Common Cathode 600 = Reverse Voltage [V]

HB = TO-247AD (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DHG 60 C 600 HB	DHG60C600HB	Tube	30	503108



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